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Break (16:35-16:45)

Session for Students Poster (5/14, 16:45-18:30)

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Keynote Speeches (II)

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K-4 (p.20) Solving Complex Global Problems: Emerging Opportunities for
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M. Imade¹, M. Uemura¹, F. Kawamura¹, M. Yoshimura¹, Y. Kitaoka¹,
Y. Mori¹, T. Sasaki¹, S. Itoh², H. Okuda², M. Yamazaki² (¹Osaka
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T. Kitayama, H. Minari, N. Mori (Osaka University)

13:15-13:30

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V. Ryzhii^{1,2}, M. Ryzhii^{1,2}, M. S. Shur³, V. Mitin⁴ (¹University of Aizu,
²Japan Science and Technology Agency, ³Rensselaer Polytechnic
Institute, ⁴University of Buffalo)

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- B-4 (p.44)** Coulomb Blockade and Hopping Conduction in Si Quantum Dot
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M. Inada¹, M. Gibo², H. Yamamoto², I. Umezu², T. Saitoh¹, A.
Sugimura² (¹Kansai University, ²Konan University)

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- B-5 (p.46)** Study of Electronic State in Electrode for Nano-Electronic Devices
M. Muraguchi¹, S. Nomura², Y. Takada², K. Shiraishi², T. Endoh¹

(¹Tohoku University, ²University of Tsukuba)

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M. Hashimoto, Y. Seiwa, K. Tuji, K. Koike, S. Sasa, M. Inoue, M. Yano (Osaka Institute of Technology)

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M. Morifuji, Y. Nakaya, T. Mitamura, M. Kondow (Osaka University)

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N. Watanabe^{1,3}, I. Tsunoda^{2,3}, T. Asano¹ (¹Kyushu University, ²Kyushu Institute of Technology, ³Fukuoka Industry, Science & Technology Foundation)

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T. Yamashita¹, Y. Sugawara¹, Y. Uraoka¹, T. Fuyuki¹, M. Kimura²
(¹Nara Institute of Science and Technology, ²Ryukoku University)

Break (16:35-16:50)

Special Invited Session for the Conference Theme

“Frontier Technologies for Ecological Society”

16:50-17:15

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T. Kimoto, J. Suda, M. Noborio, T. Hiyoshi (Kyoto University)

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T-2 (p.26) Printable and Flexible Organic Light Emitting Devices for Sustainable Future

Y. Ohmori (Osaka University)

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Awards & Closing Remark

17:50-18:00 Award Presentation: T. Nishimura (Renesas Technology Corp.)

18:00-18:05 Closing Remark: T. Nishimura (Renesas Technology Corp.)